P-Channel 100-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

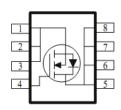
- White LED boost converters
- · Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY					
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)			
-100	95 @ V _{GS} = -10V	-33			
	125 @ V _{GS} = -4.5V	-29			



FREE





ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter				Limit	Units		
Drain-Source Voltage				-100	V		
Gate-Source Voltage				±20	V		
	T _C =25	5°C	- I _D	-33	А		
Continuous Drain Current	T _C =70)°C		-26			
	T _A =25	5°C		-6 ^a			
	T _A =70)°C		-4.7 ^a			
Pulsed Drain Current ^b				-40			
Continuous Source Current (Diode Conduction) a		I _S	-6	ı			
	T _C =25	5°C	В	156	W		
Power Dissipation	T _C =70)°C		100			
Fower Dissipation	T _A =25°C		P _D	5 ^a	VV		
	T _A =70)°C		3.2 ^a			
Operating Junction and Storage Temperature Range				-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
IMAXIMUM JUNCUON-to-Ambient	Steady State	IXOJA	65				
Maximum Junction-to-Case	Steady State	$R_{\theta JC}$	0.8				

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

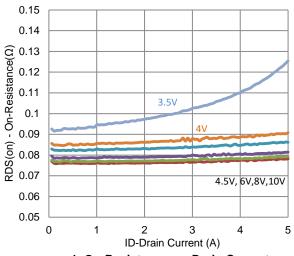
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}$			-1	-1 uA	
Zero Gate Voltage Brain Garrent	.099	$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-5	uд	
On-State Drain Current	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-5			Α	
Drain-Source On-Resistance	r	$V_{GS} = -10 \text{ V}, I_{D} = -3.0 \text{ A}$			95	mΩ	
Diain-Source On-Resistance	r _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -2.9 \text{ A}$			125	11122	
Forward Transconductance	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -3.0 \text{ A}$		10		S	
Diode Forward Voltage	V_{SD}	$I_S = -2.9 \text{ A}, V_{GS} = 0 \text{ V}$		0.8		V	
		Dynamic					
Total Gate Charge	Q_g			30			
Gate-Source Charge	Q_{gs}	$V_{DS} = -50 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -3 \text{ A}$		12		nC	
Gate-Drain Charge	Q_{gd}			14			
Turn-On Delay Time	t _{d(on)}			7			
Rise Time	t _r	$V_{DD} = -50 \text{ V}, R_L = 16.7 \Omega, I_D = -3 \text{ A},$		18		ne	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		151		ns	
Fall Time	t _f			143			
Input Capacitance	C_{iss}			3665			
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		383		pF	
Reverse Transfer Capacitance	C _{rss}			189			

Notes

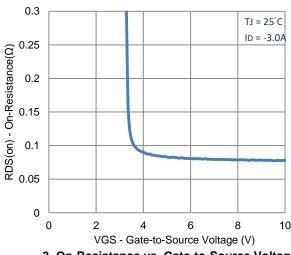
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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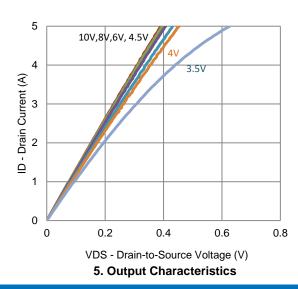
Typical Electrical Characteristics



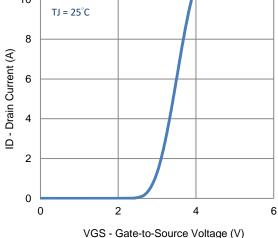
1. On-Resistance vs. Drain Current



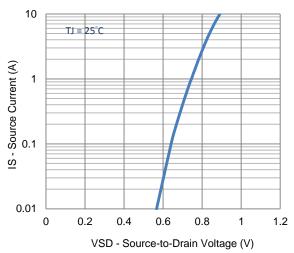
3. On-Resistance vs. Gate-to-Source Voltage



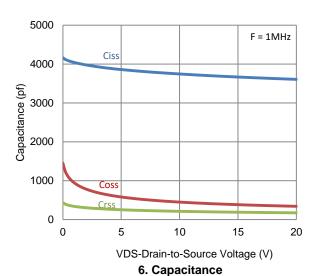
10 TJ = 25°C



2. Transfer Characteristics

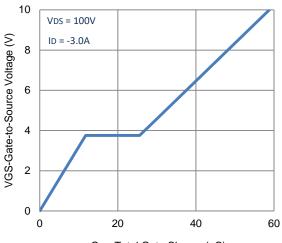


4. Drain-to-Source Forward Voltage

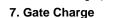


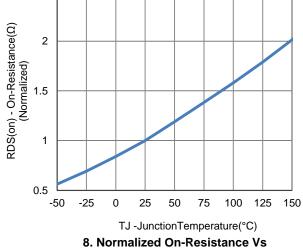
Typical Electrical Characteristics

2.5

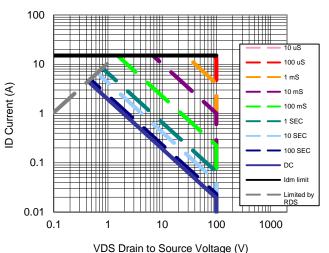


Qg - Total Gate Charge (nC)

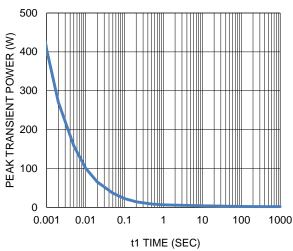




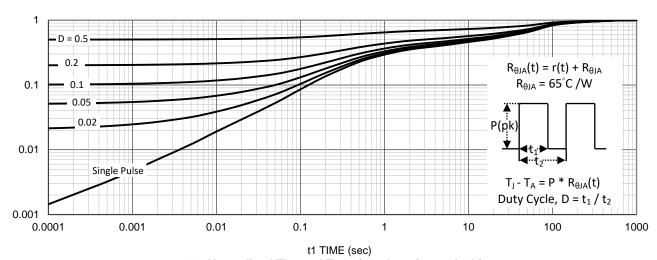
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

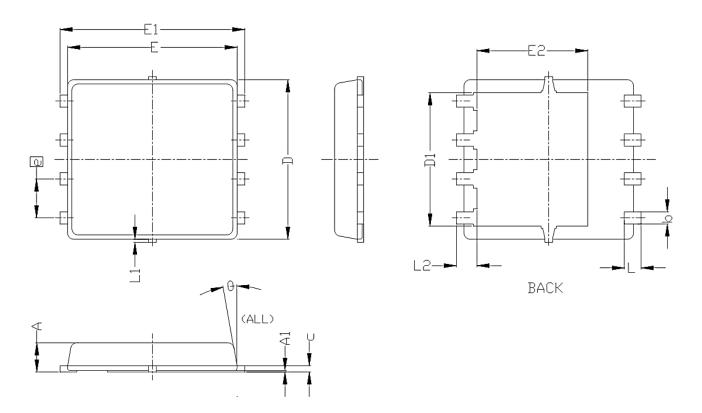


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES				
MIN		NOM	MAX	MIN	NOM	MAX	
Α	0.85	0.95	1.00	0.033	0.037	0. 039	
A1	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0. 15	0.20	0.25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1	4. 35 BSC			0. 171 BSC			
E	5, 55 BSC			0, 219 BSC			
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0. 050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0. 15	0		0.006	
L2	0.68 REF			0. 027 REF			
θ	0°		10°	0° 1		10°	